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ABSTRACT

METHOD OF SEMICONDUCTOR MANUFACTURE

A method is provided to apply a metal layer to a semiconductor wafer which avoids the sputtering process. Instead, a thin metal foil is thermo-compressed to the semiconductor wafer with a layer of dielectric material in-between the wafer and the metal foil. This is much quicker and less expensive than the sputtering process. Further, an interconnect between the bond pad and metal layer may be provided by an electroless nickel plating method.

Figures 2 (a-c)



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